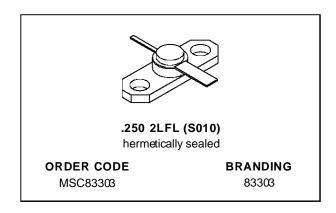


MSC83303

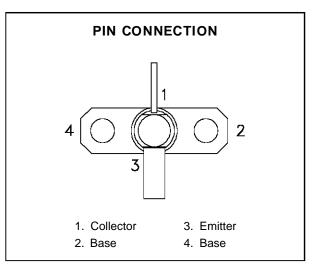
RF & MICROWAVE TRANSISTORS GENERAL PURPOSE AMPLIFIER APPLICATIONS

- REFRACTORY/GOLD METALLIZATION
- EMITTER BALLASTED
- VSWR CAPABILITY ∞:1 @ RATED CONDITIONS
- HERMETIC STRIPAC® PACKAGE
- P_{OUT} = 3.0 W MIN. WITH 7.0 dB GAIN @ 3.0 GHz



DESCRIPTION

The MSC83303 is a common base hermetically sealed silicon NPN microwave power transistor utilizing an overlay, emitter site ballasted geometry with a refractory/gold metallization system. This device is capable of withstanding an infinite load VSWR at any phase angle under rated conditions. The MSC83303 is designed for Class C amplifier/oscillator applications in the 1.0 - 3.0 GHz frequency range.



ABSOLUTE MAXIMUM RATINGS $(T_{case} = 25^{\circ}C)$

Symbol	Parameter	Value	Unit
Poiss	Power Dissipation* (T _C ≤ 50°C)	10.0	W
Ic	Device Current*	540	mA
Vcc	Collector-Supply Voltage*	30	V
TJ	Junction Temperature	200	°C
T _{STG}	Storage Temperature	- 65 to +200	°C

THERMAL DATA

R _{TH(j-c)} Junction-Case Thermal Resistance*	12	°C/W
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^{*}Applies only to rated RF amplifier operation

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ELECTRICAL SPECIFICATIONS $(T_{case} = 25^{\circ}C)$

STATIC

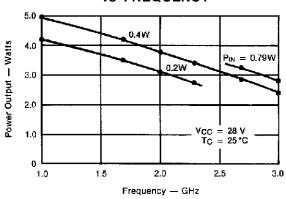
Cumb a l	Took Conditions	Value			11:4		
Symbol	Test Conditions		Min.	Тур.	Max.	Unit	
BV _{CBO}	I _C = 1 mA	$I_E = 0 \text{ mA}$		45	_		V
BV _{EBO}	I _E = 1 mA	$I_C = 0 \text{ mA}$		3.5	_	_	V
BVcer	I _C = 5 mA	$R_{BE} = 10 \Omega$		45	_		V
Ісво	V _{CB} = 28 V			_	_	0.5	mA
h _{FE}	V _{CE} = 5 V	$I_C = 200 \text{ mA}$		30	_	300	_

DYNAMIC

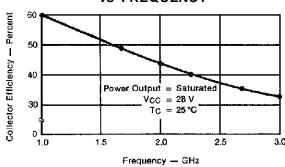
Symbol	Took Conditions			Value			
Symbol		Test Conditions		Min.	Тур.	Max.	Unit
Роит	f = 3.0 GHz	$P_{IN} = 0.79 \text{ W}$	$V_{CC} = 28 \text{ V}$	2.5	2.8	_	W
ης	f = 3.0 GHz	$P_{IN} = 0.79 \text{ W}$	$V_{CC} = 28 \text{ V}$	30	33	_	%
P _G	f = 3.0 GHz	$P_{IN} = 0.79 \text{ W}$	$V_{CC} = 28 \text{ V}$	5.0	5.5	_	dB
Сов	f = 1 MHz	V _{CB} = 28 V		_	_	5	pF

TYPICAL PERFORMANCE

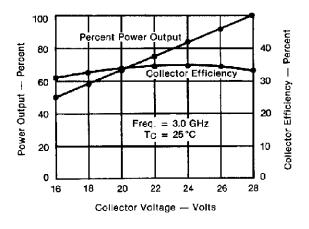
TYPICAL POWER OUTPUT vs FREQUENCY



TYPICAL COLLECTOR EFFICIENCY vs FREQUENCY

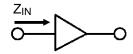


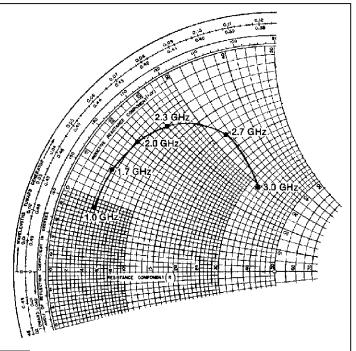
PERCENT POWER OUTPUT & COLLECTOR EFFICIENCY vs COLLECTOR VOLTAGE



IMPEDANCE DATA

TYPICAL INPUT IMPEDANCE

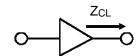


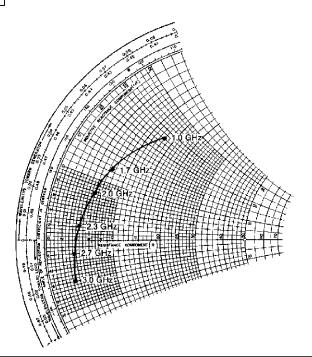


FREQ.	Z _{IN} (Ω)	Z _{CL} (Ω)
1.0 GHz	4.4 + j 8.7	13.0 + j 23.0
1.7 GHz	4.5 + j 14.5	7.5 + j 12.5
2.0 GHz	5.1 + j 20.0	6.0 + j 7.8
2.3 GHz	7.0 + j 25.0	4.5 + j 2.2
2.7 GHz	16.0 + j 33.0	3.8 – j 2.0
3.0 GHz	33.0 + j 29.0	3.3 – j 6.0

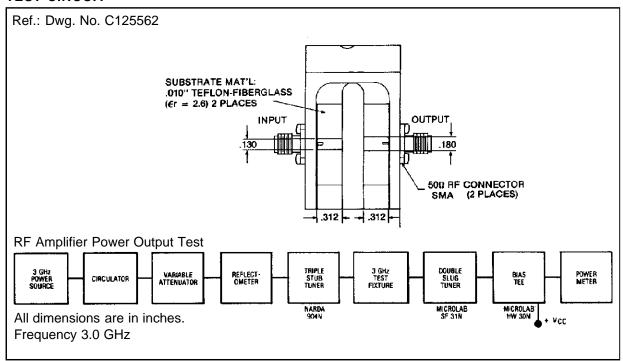
 $P_{OUT} = Saturated$ $V_{CC} = 28 V$ Normalized to 50 ohms

TYPICAL COLLECTOR LOAD IMPEDANCE

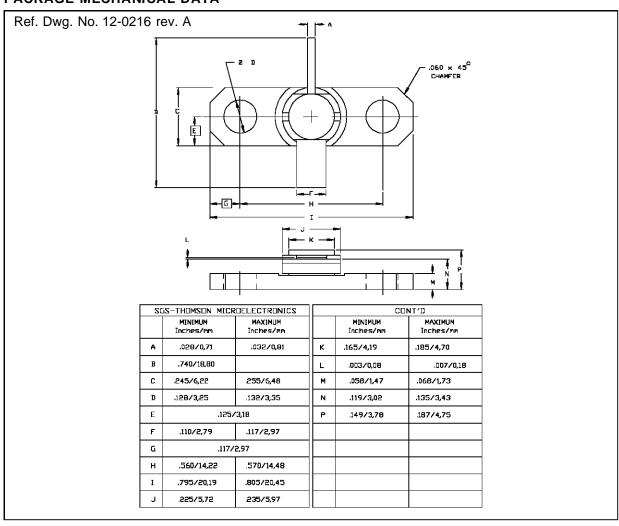




TEST CIRCUIT



PACKAGE MECHANICAL DATA



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